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(54) **DISPLAY DEVICE AND ELECTRONIC DEVICE INCLUDING THE DISPLAY DEVICE**

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(57) **ABSTRACT**

The display device includes a first substrate provided with a driver circuit region that is located outside and adjacent to a pixel region and includes at least one second transistor which supplies a signal to the first transistor in each of the pixels in the pixel region, a second substrate facing the first substrate, a liquid crystal layer between the first substrate and the second substrate, a first interlayer insulating film including an inorganic insulating material over the first transistor and the second transistor, a second interlayer insulating film including an organic insulating material over the first interlayer insulating film, and a third interlayer insulating film including an inorganic insulating material over the second interlayer insulating film. The third interlayer insulating film is provided in part of an upper region of the pixel region, and has an edge portion on an inner side than the driver circuit region.

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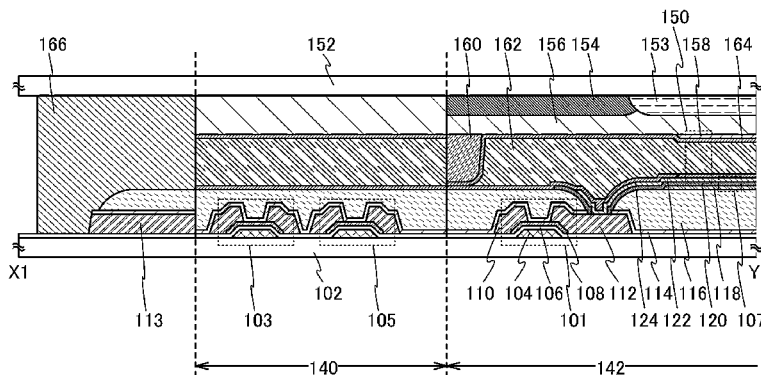
CPC **G02F 1/1368** (2013.01); **G02F 1/1345** (2013.01); **H01L 27/1214** (2013.01); **H01L 27/1225** (2013.01); **H01L 27/1248** (2013.01); **G02F 1/133345** (2013.01)

(58) **Field of Classification Search**

None

See application file for complete search history.

27 Claims, 11 Drawing Sheets



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